

关键参数 Key Parameters

V_{CES}		3300	V
$V_{CE(sat)}$	Typ.	2.60	V
I_C	Max.	1500	A
$I_{C(RM)}$	Max.	3000	A

典型应用 Typical Applications

- 牵引传动 Traction Drives
- 电机控制 Motor Controllers
- 智能电网 Smart Grid
- 高可靠性逆变器 High Reliability Inverters

特点 Features

- AISiC 基板 AISiC Baseplate
- AlN 衬板 AlN Substrates
- 高热循环能力 High Thermal Cycling Capability
- 10 μ s 短路承受能力 10 μ s Short Circuit Withstand

电路结构 Circuit Configuration

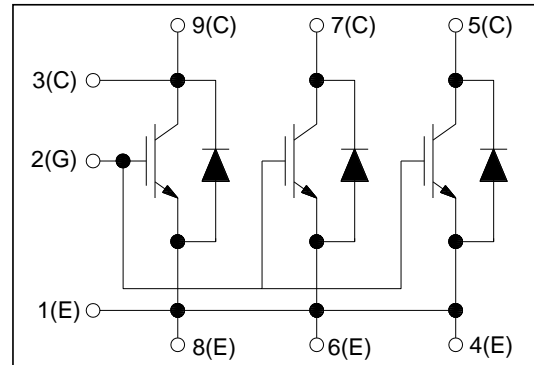


图 1. 电路结构

Fig. 1 Circuit configuration

模块外形 Module Appearance



图 2. 模块外形

Fig. 2 Module appearance

模块标签说明

Module Label Code Instruction



ab1234567890

数据位置 Data position	数据内容 Content of data
1--8	模块批次号 Module batch number
9--12	模块序列号 Module serial number

最大额定值
Absolute Maximum Ratings

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
V_{CES}	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^\circ\text{C}$	3300	V
V_{GES}	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^\circ\text{C}$	± 20	V
I_C	集电极电流 Collector-emitter current	$T_C = 95\text{ }^\circ\text{C}$	1500	A
$I_{C(RM)}$	集电极峰值电流 Peak collector current	$t_p = 1\text{ms}$	3000	A
P_{max}	晶体管部分最大损耗 Max. transistor power dissipation	$T_{vj} = 150\text{ }^\circ\text{C}, T_C = 25\text{ }^\circ\text{C}$	14.8	kW
ρ_t	二极管 ρ_t 值 Diode ρ_t	$V_R = 0V, t_p = 10\text{ms}, T_{vj} = 150\text{ }^\circ\text{C}$	720	kA^2s
V_{isol}	绝缘电压(模块) Isolation voltage – per module	短接所有端子, 端子与基板间施加电压 (Connected terminals to base plate), AC RMS, 1 min, 50Hz, $T_C = 25\text{ }^\circ\text{C}$	6000	V
Q_{PD}	局部放电电荷(模块) Partial discharge – per module	IEC1287. $V_1 = 3500V, V_2 = 2600V, 50\text{Hz RMS}$	10	pC

热和机械数据
Thermal & Mechanical Data

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	33.0	mm
	端子-端子 Terminal to terminal	34.0	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	20.0	mm
	端子-端子 Terminal to terminal	20.0	mm
相对漏电起痕指数 CTI (Comparative Tracking Index)		>600	

热和机械数据

Thermal & Mechanical Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{th(J-C) IGBT}$	IGBT 结壳热阻 Thermal resistance – IGBT				8.4	K / kW
$R_{th(J-C) Diode}$	二极管结壳热阻 Thermal resistance – Diode				12.8	K / kW
$R_{th(C-H)}$	接触热阻(模块) Thermal resistance – case to heatsink (per module)	安装力矩 5Nm, 导热脂 1W/m·K Mounting torque 5Nm, with mounting grease 1W/m·K		6		K / kW
$T_{vj op}$	工作结温 Operating junction temperature	IGBT 芯片(IGBT)	-40		150	°C
		二极管芯片(Diode)	-40		150	°C
T_{stg}	存储温度 Storage temperature range		-40		150	°C
M	安装力矩 Screw torque	安装紧固用 – M6 Mounting – M6			5	Nm
		电路互连用 – M4 Electrical connections – M4			2	Nm
		电路互连用 – M8 Electrical connections – M8			10	Nm

电特性值
Electrical Characteristics

 除非特别声明, 否则 $T_C = 25\text{ }^\circ\text{C}$
 $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{CES}	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{vj} = 125\text{ }^\circ\text{C}$			90	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{vj} = 150\text{ }^\circ\text{C}$			150	mA
I_{GES}	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			1	μA
$V_{GE(th)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 120\text{mA}, V_{GE} = V_{CE}$	5.40	6.00	6.60	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 1500A$		2.60	3.00	V
		$V_{GE} = 15V, I_C = 1500A, T_{vj} = 125\text{ }^\circ\text{C}$		3.15		V
		$V_{GE} = 15V, I_C = 1500A, T_{vj} = 150\text{ }^\circ\text{C}$		3.30		V
I_F	二极管正向直流电流 Diode forward current	DC		1500		A
I_{FRM}	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1\text{ms}$		3000		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 1500A, V_{GE} = 0V$		2.00	2.40	V
		$I_F = 1500A, V_{GE} = 0V, T_{vj} = 125\text{ }^\circ\text{C}$		2.15		V
		$I_F = 1500A, V_{GE} = 0V, T_{vj} = 150\text{ }^\circ\text{C}$		2.15		V
I_{SC}	短路电流 Short circuit current	$T_{vj} = 150\text{ }^\circ\text{C}, V_{CC} = 2500V,$ $V_{GE} \leq 15V, t_p \leq 10\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 60747-9		6700		A

- 注意:** 1.(*1) 表示该参数的测试点为辅助母排端子 (*1) indicates it is measured at the auxiliary busbar terminal),
Note: 2.(*2) 表示 L 是电路杂散电感加上 L_{sCE} (*2) indicates L is the circuit stray inductance plus L_M).

电特性值
Electrical Characteristics

 除非特别声明，否则 $T_C = 25\text{ }^\circ\text{C}$
 $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
C_{ies}	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		158		nF
Q_g	栅极电荷 Gate charge	$\pm 15V$		14		μC
C_{res}	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		3.7		nF
L_{sCE}	模块杂散电感 Module stray inductance			5		nH
$R_{CC'+EE'}$	模块引线电阻，端子-芯片 Module lead resistance, terminal-chip			140		$\mu\Omega$

电特性值

Electrical Characteristics

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit	
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 1500A,$ $V_{CE} = 1800V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 1.5\Omega$ $C_{GE} = 330nF,$ $L_S = 180nH,$ $dv/dt = 4700V/\mu s$ ($T_{vj} = 150^\circ C$).	$T_{vj} = 25^\circ C$	2450		ns	
			$T_{vj} = 125^\circ C$	2530			
			$T_{vj} = 150^\circ C$	2550			
t_f	下降时间 Fall time		$T_{vj} = 25^\circ C$		1300		ns
			$T_{vj} = 125^\circ C$		2050		
			$T_{vj} = 150^\circ C$		2260		
E_{OFF}	关断损耗 Turn-off energy loss	$T_{vj} = 25^\circ C$		2365		mJ	
		$T_{vj} = 125^\circ C$		2930			
		$T_{vj} = 150^\circ C$		3100			
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$I_C = 1500A,$ $V_{CE} = 1800V,$ $V_{GE} = \pm 15V,$ $R_{G(ON)} = 1.0\Omega,$ $C_{GE} = 330nF,$ $L_S = 180nH,$ $di/dt = 3700A/\mu s$ ($T_{vj} = 150^\circ C$).	$T_{vj} = 25^\circ C$		550	ns	
			$T_{vj} = 125^\circ C$		585		
			$T_{vj} = 150^\circ C$		585		
t_r	上升时间 Rise time		$T_{vj} = 25^\circ C$		355		ns
			$T_{vj} = 125^\circ C$		363		
			$T_{vj} = 150^\circ C$		370		
E_{ON}	开通损耗 Turn-on energy loss	$T_{vj} = 25^\circ C$		1360		mJ	
		$T_{vj} = 125^\circ C$		1730			
		$T_{vj} = 150^\circ C$		2000			
Q_{rr}	二极管反向恢复电荷 Diode reverse recovery charge	$I_F = 1500A,$ $V_{CE} = 1800V,$ $-di_F/dt = 3700A/\mu s$ ($T_{vj} = 150^\circ C$).	$T_{vj} = 25^\circ C$		1130	μC	
			$T_{vj} = 125^\circ C$		1700		
			$T_{vj} = 150^\circ C$		1950		
I_{rr}	二极管反向恢复电流 Diode reverse recovery current		$T_{vj} = 25^\circ C$		1460		A
			$T_{vj} = 125^\circ C$		1580		
			$T_{vj} = 150^\circ C$		1660		
E_{rec}	二极管反向恢复损耗 Diode reverse recovery energy	$T_{vj} = 25^\circ C$		1490		mJ	
		$T_{vj} = 125^\circ C$		2310			
		$T_{vj} = 150^\circ C$		2700			

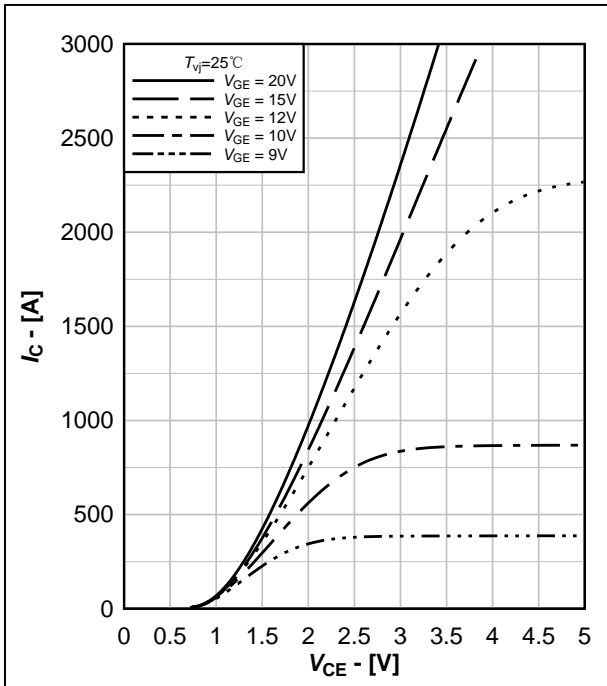


图 3. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.3 Typical IGBT output characteristics, $I_C = f(V_{CE})$

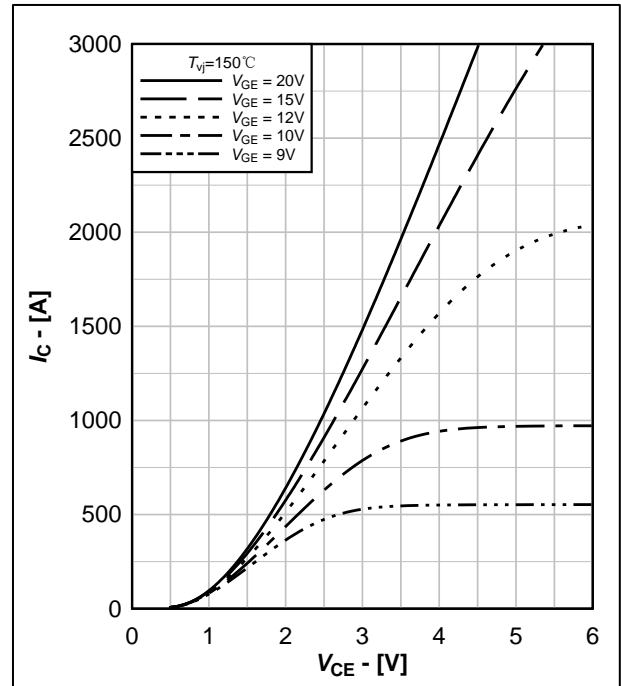


图 4. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.4 Typical IGBT output characteristics, $I_C = f(V_{CE})$

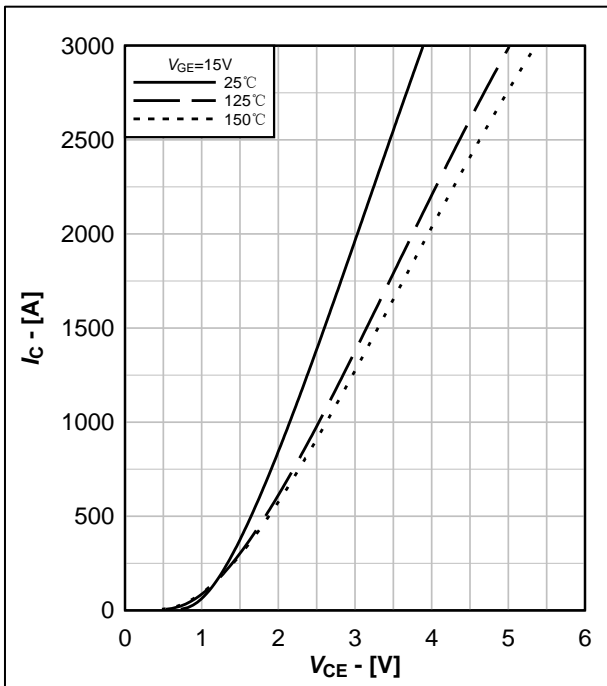


图 5. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.5 Typical IGBT output characteristics, $I_C = f(V_{CE})$

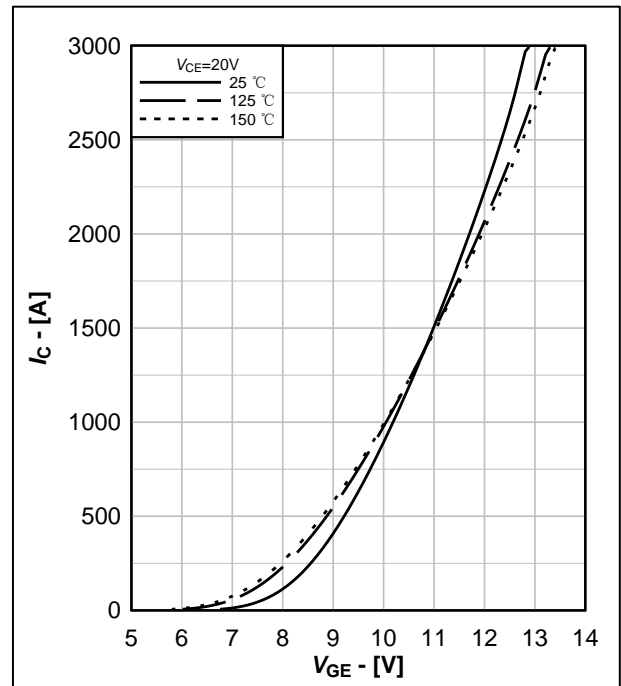


图 6. IGBT 传输特性典型曲线, $I_C = f(V_{GE})$

Fig.6 Typical IGBT transfer characteristics, $I_C = f(V_{GE})$

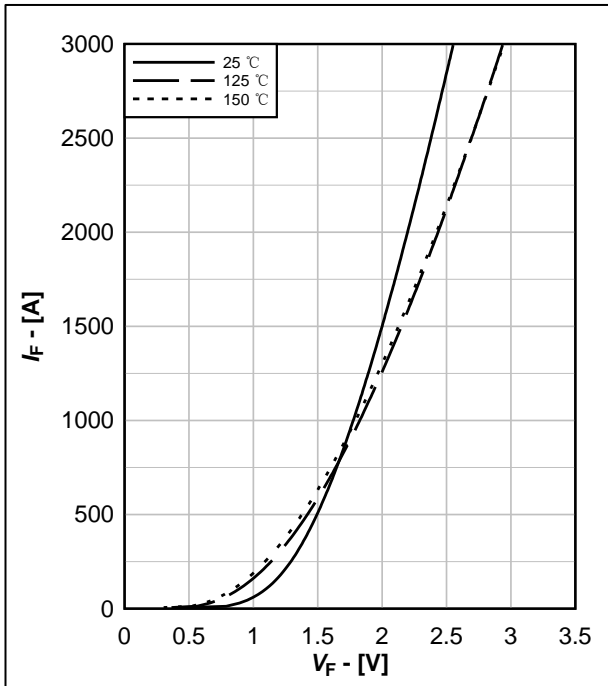


图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$

Fig.7 Typical FRD output characteristics, $I_F = f(V_F)$

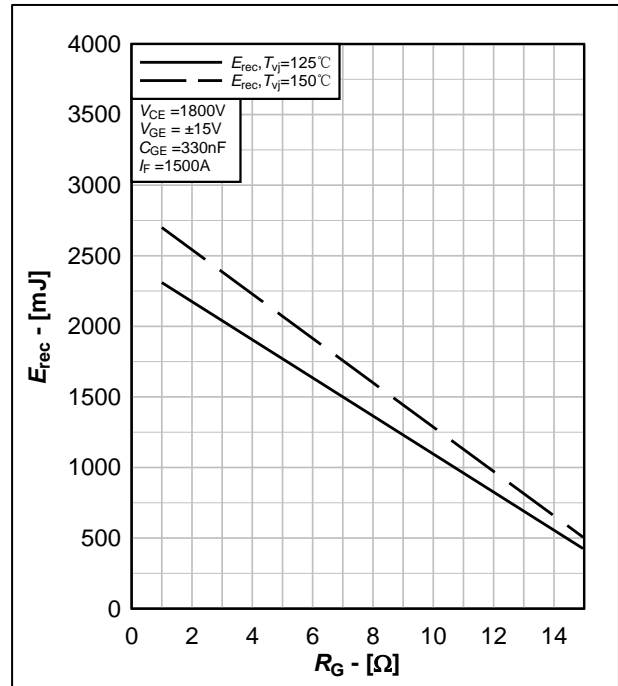


图 8. FRD 反向恢复损耗典型曲线, $E_{rec} = f(R_G)$

Fig.8 Typical FRD switching loss E_{rec} , $E_{rec} = f(R_G)$

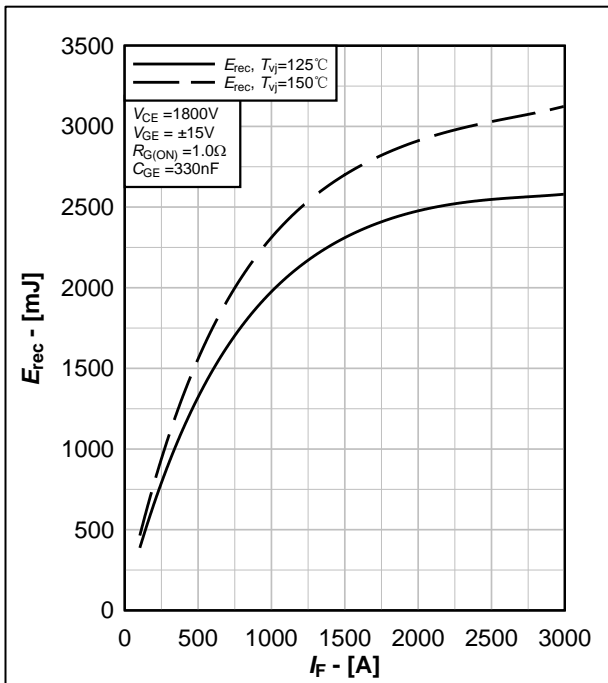


图 9. FRD 反向恢复损耗典型曲线, $E_{rec} = f(I_F)$

Fig.9 Typical FRD switching loss E_{rec} , $E_{rec} = f(I_F)$

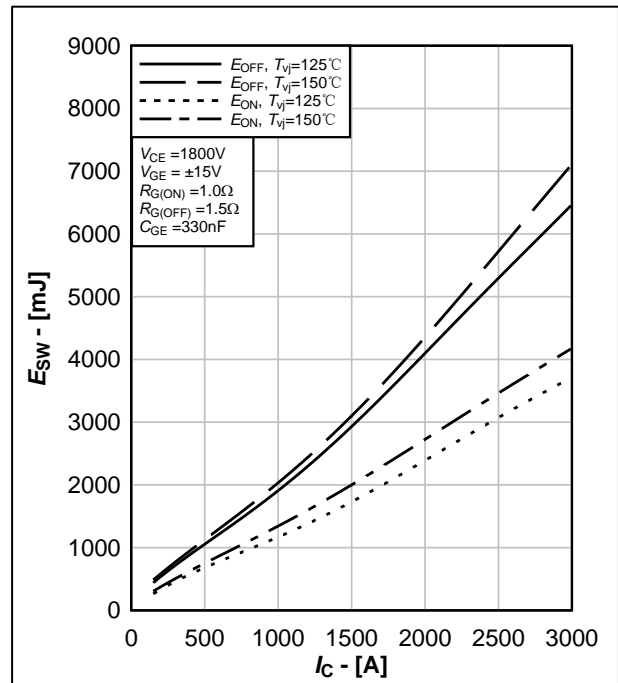


图 10. IGBT 开关损耗典型曲线, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

Fig.10 Typical IGBT switching loss, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

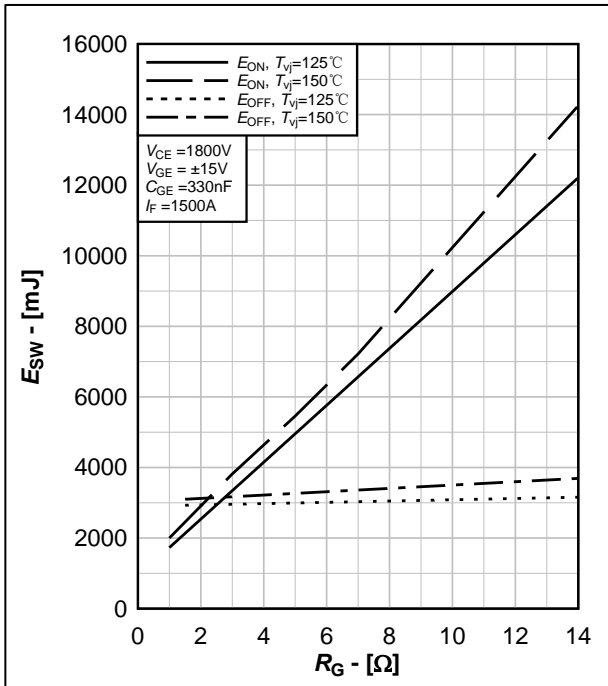


图 11. IGBT 开关损耗典型曲线, $E_{on} = f(R_G)$, $E_{off} = f(R_G)$

Fig.11 Typical IGBT switching loss, $E_{on} = f(R_G)$, $E_{off} = f(R_G)$

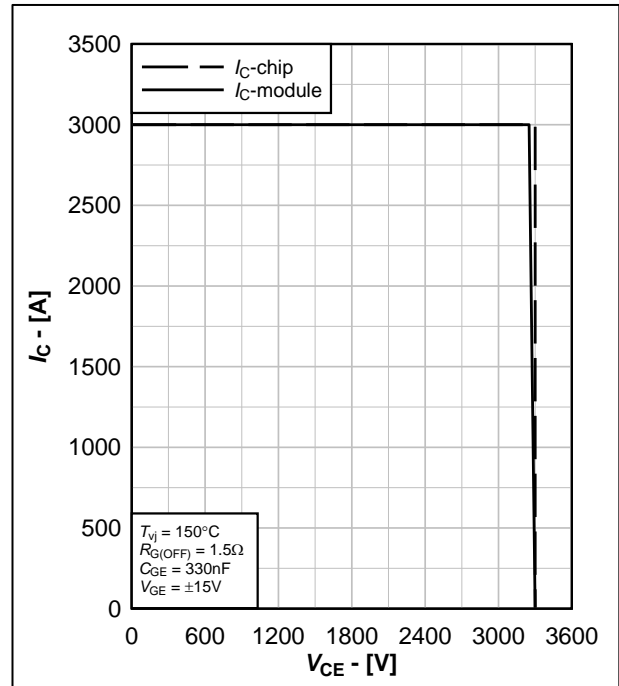


图 12. IGBT 反偏安全工作区, $I_C = f(V_{CE})$

Fig.12 Reverse bias safe operating area of IGBT, $I_C = f(V_{CE})$

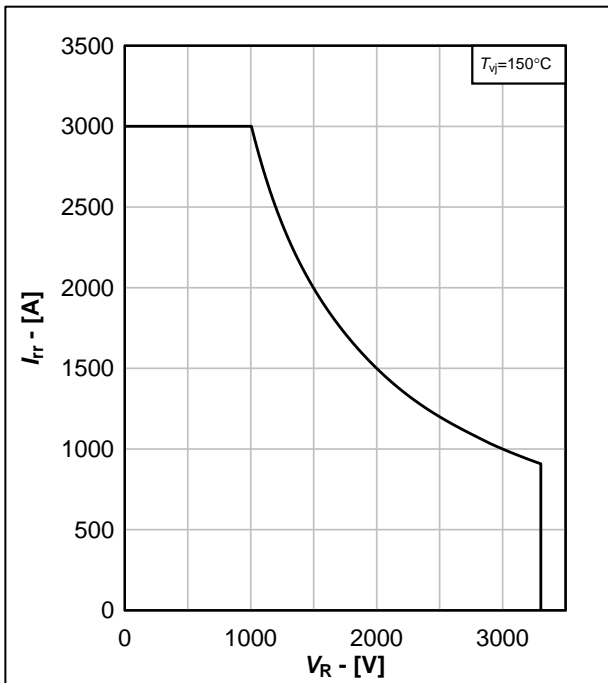


图 13. FRD 反偏安全工作区, $I_{rr} = f(V_R)$

Fig.13 Reverse bias safe operating area of FRD, $I_{rr} = f(V_R)$

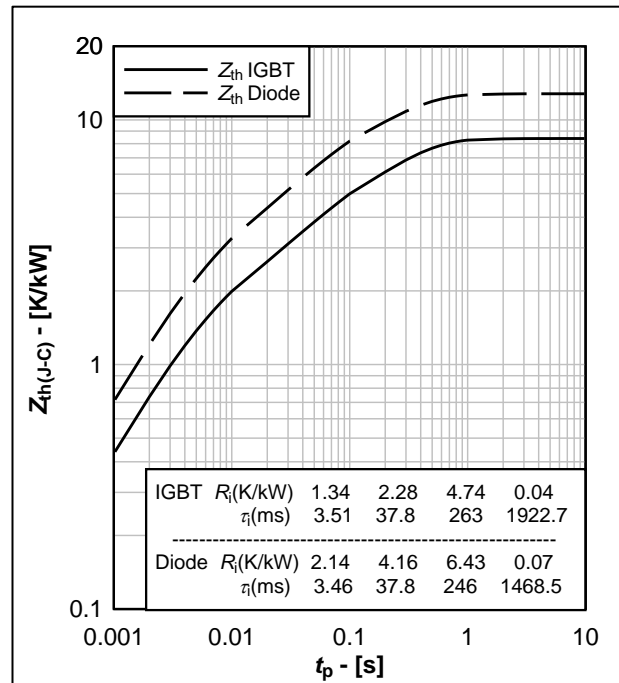
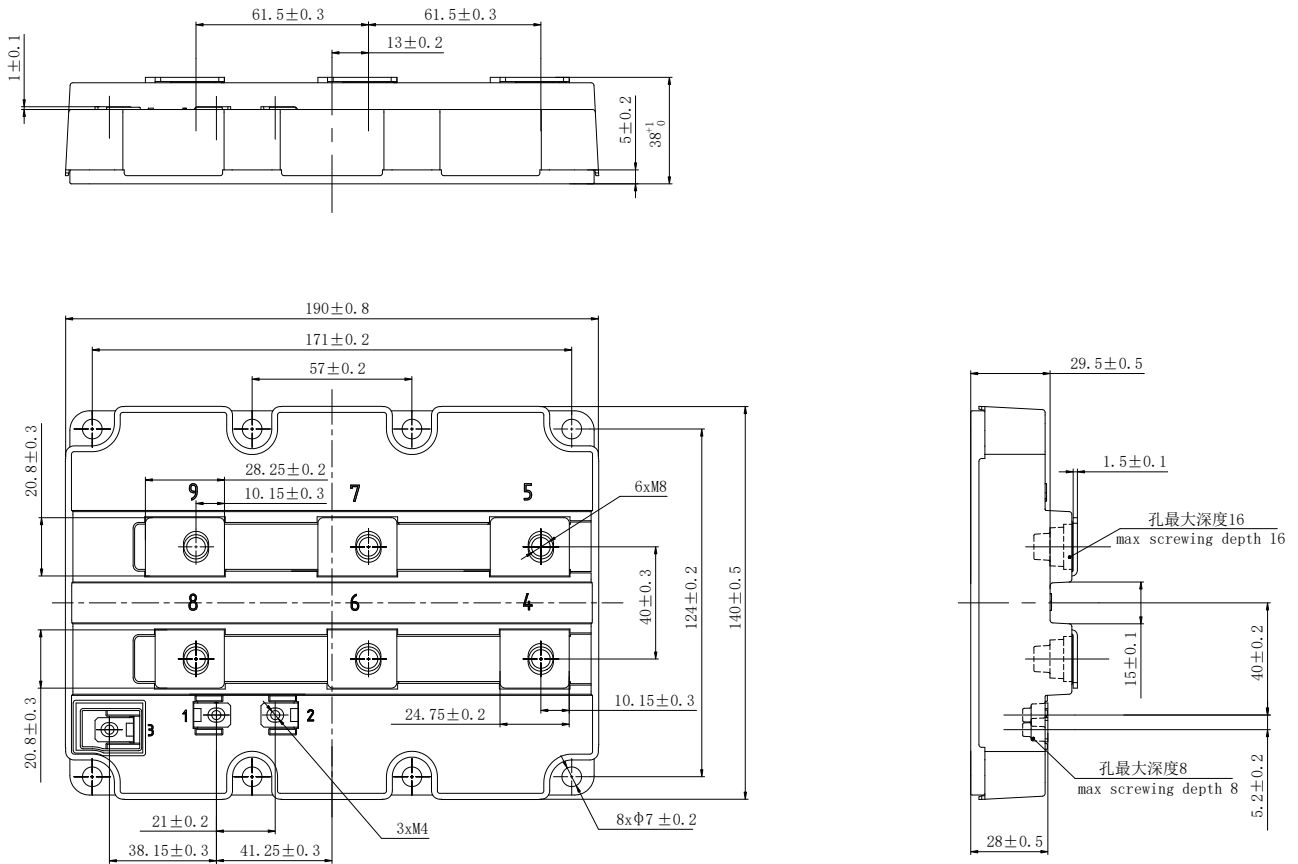


图 14. 瞬态热阻抗曲线, $Z_{th(j-c)} = f(t_p)$

Fig.14 Transient thermal impedance, $Z_{th(j-c)} = f(t_p)$



重量 Weight: 1100g 模块外观类型 Module outline code: E2

图 15. 模块外观尺寸

Fig. 15 Module outlines

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